

Product Summary

| BV_{DSS} | $R_{DS(ON)}$ Max | I_D $T_A = +25^\circ C$ |
|------------|------------------------|------------------------------|
| 20V | 0.4Ω @ $V_{GS} = 4.5V$ | 1A |
| | 0.7Ω @ $V_{GS} = 1.8V$ | 0.8A |

Features and Benefits

- Low On-Resistance
- Very Low Gate Threshold Voltage $V_{GS(TH)}$, 1.0V Max.
- Low Input Capacitance
- Fast Switching Speed
- Ultra-Small Surfaced Mount Package
- Ultra-Low Package Profile, 0.4mm Maximum Package Height
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

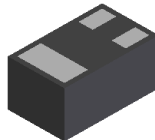
- DC-DC Converters
- Power Management Functions

Mechanical Data

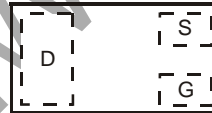
- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 ⁽⁴⁾
- Weight: 0.001 grams (Approximate)



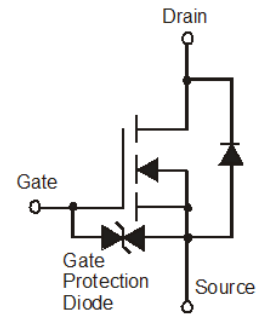
X2-DFN1006-3



Bottom View



Top View
Internal Schematic





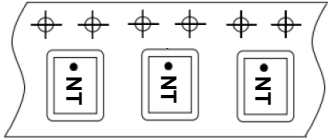
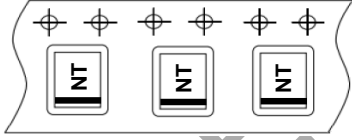

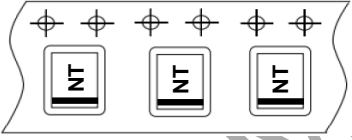
EQUIVALENT CIRCUIT

Ordering Information (Note 4)

| Part Number | Case | Packaging |
|----------------|--------------|--------------------|
| DMN2500UFB4-7 | X2-DFN1006-3 | 3,000/Tape & Reel |
| DMN2500UFB4-7B | X2-DFN1006-3 | 10,000/Tape & Reel |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

| | |
|------------------------------|--|
| <p>DMN2500UFB4-7</p> | <div style="display: flex; justify-content: space-around;"> <div style="text-align: center;">  <p>Top View Dot Denotes Drain Side</p> </div> <div style="text-align: center;"> <p>From date code 1527 (YYWW), this changes to:</p>  <p>Top View Bar Denotes Gate and Source Side</p> </div> </div> <div style="display: flex; justify-content: space-around; margin-top: 20px;">   </div> |
| <p>DMN2500UFB4-7B</p> | <div style="text-align: center;">  <p>Top View Bar Denotes Gate and Source Side</p> </div> <div style="text-align: center; margin-top: 20px;">  <p>NT = Part Marking Code</p> </div> |

NOT RECOMMENDED FOR NEW DESIGN

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Unit |
|--|--------------|--|------------------|--------------|------|
| Drain-Source Voltage | | | V _{DSS} | 20 | V |
| Gate-Source Voltage | | | V _{GSS} | ±6 | V |
| Continuous Drain Current (Note 5) V _{GS} = 4.5V | Steady State | T _A = +25°C T _A = +70°C | I _D | 810 640 | mA |
| | t < 10s | T _A = +25°C T _A = +70°C | I _D | 950 750 | mA |
| Continuous Drain Current (Note 6) V _{GS} = 4.5V | Steady State | T _A = +25°C T _A = +70°C | I _D | 1000 800 | mA |
| | t < 10s | T _A = +25°C T _A = +70°C | I _D | 1200 1000 | mA |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) | | | I _{DM} | 4 | A |
| Maximum Body Diode Continuous Current | | | I _S | 850 | mA |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | Symbol | Value | Unit |
|--|------------------------|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 5) | T _A = +25°C | P _D | 0.46 | W |
| | T _A = +70°C | | 0.29 | |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State | R _{θJA} | 279 | °C/W |
| | t < 10s | | 210 | °C/W |
| Total Power Dissipation (Note 6) | T _A = +25°C | P _D | 0.95 | W |
| | T _A = +70°C | | 0.6 | |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State | R _{θJA} | 134 | °C/W |
| | t < 10s | | 100 | °C/W |
| Operating and Storage Temperature Range | | T _J , T _{STG} | -55 to +150 | °C |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|--|---------------------|-----|-------|------|------|---|
| OFF CHARACTERISTICS (Note 7) | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 20 | - | - | V | V _{GS} = 0V, I _D = 250µA |
| Zero Gate Voltage Drain Current T _J = +25°C | I _{DSS} | - | - | 100 | nA | V _{DS} = 20V, V _{GS} = 0V |
| Gate-Source Leakage | I _{GSS} | - | - | ±1.0 | µA | V _{GS} = ±4.5V, V _{DS} = 0V |
| ON CHARACTERISTICS (Note 7) | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | 0.5 | - | 1.0 | V | V _{DS} = V _{GS} , I _D = 250µA |
| Static Drain-Source On-Resistance | R _{DS(ON)} | - | 0.3 | 0.4 | Ω | V _{GS} = 4.5V, I _D = 600mA |
| | | | 0.4 | 0.5 | | V _{GS} = 2.5V, I _D = 500mA |
| | | | 0.5 | 0.7 | | V _{GS} = 1.8V, I _D = 350mA |
| Forward Transfer Admittance | Y _{fs} | - | 1.4 | - | S | V _{DS} = 10V, I _D = 400mA |
| Diode Forward Voltage | V _{SD} | - | 0.7 | 1.2 | V | V _{GS} = 0V, I _S = 150mA |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | |
| Input Capacitance | C _{iss} | - | 60.67 | - | pF | V _{DS} = 16V, V _{GS} = 0V, f = 1.0MHz |
| Output Capacitance | C _{oss} | - | 9.68 | - | pF | |
| Reverse Transfer Capacitance | C _{rss} | - | 5.37 | - | pF | |
| Gate Resistance | R _g | - | 93 | - | Ω | V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz |
| Total Gate Charge | Q _g | - | 736.6 | - | pC | V _{GS} = 4.5V, V _{DS} = 10V, I _D = 250mA |
| Gate-Source Charge | Q _{gs} | - | 93.6 | - | pC | |
| Gate-Drain Charge | Q _{gd} | - | 116.6 | - | pC | |
| Turn-On Delay Time | t _{d(ON)} | - | 5.1 | - | ns | V _{DD} = 10V, V _{GS} = 4.5V, R _L = 47Ω, R _G = 10Ω, I _D = 200mA |
| Turn-On Rise Time | t _R | - | 7.4 | - | ns | |
| Turn-Off Delay Time | t _{d(OFF)} | - | 26.7 | - | ns | |
| Turn-Off Fall Time | t _F | - | 12.3 | - | ns | |

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.

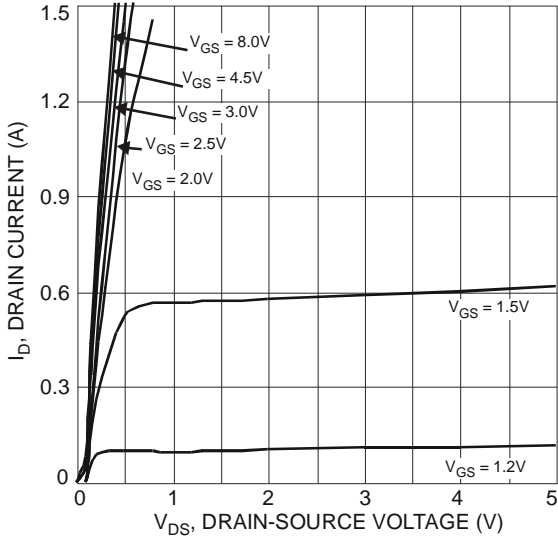


Fig. 1 Typical Output Characteristics

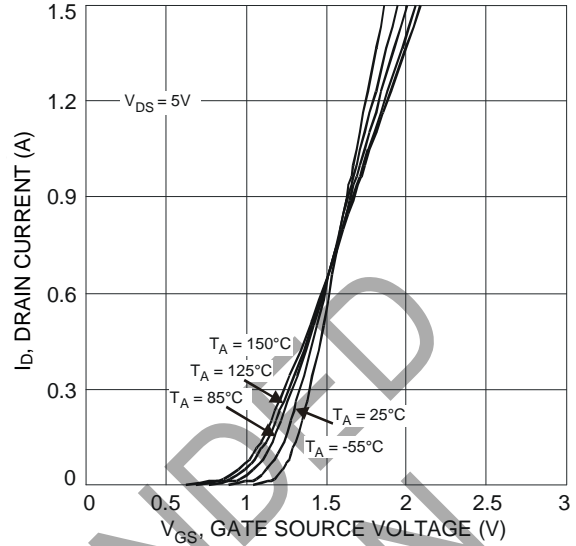


Fig. 2 Typical Transfer Characteristics

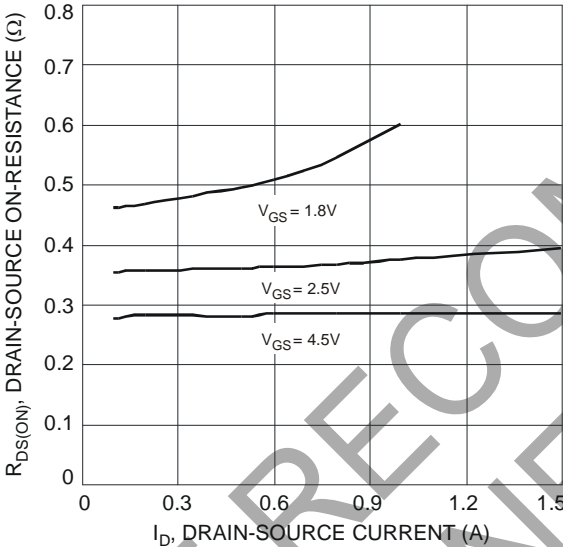


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

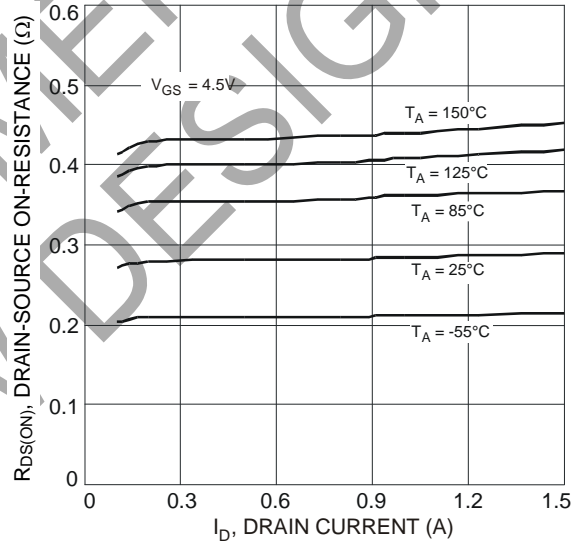


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

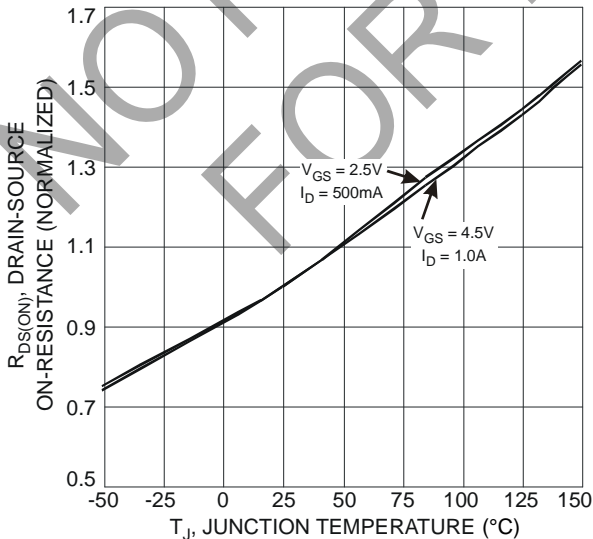


Fig. 5 On-Resistance Variation with Temperature

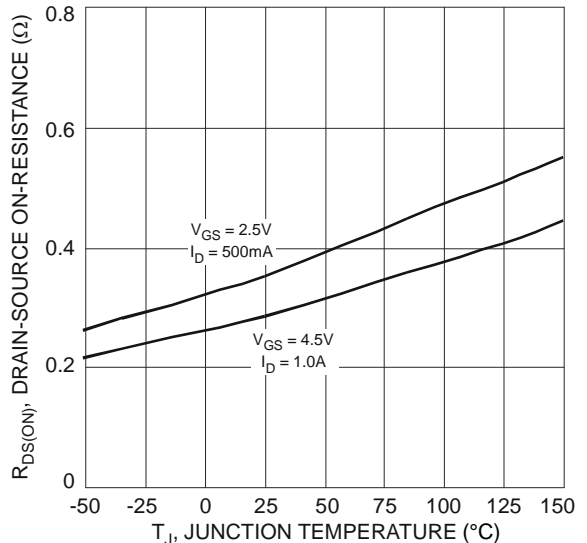


Fig. 6 On-Resistance Variation with Temperature

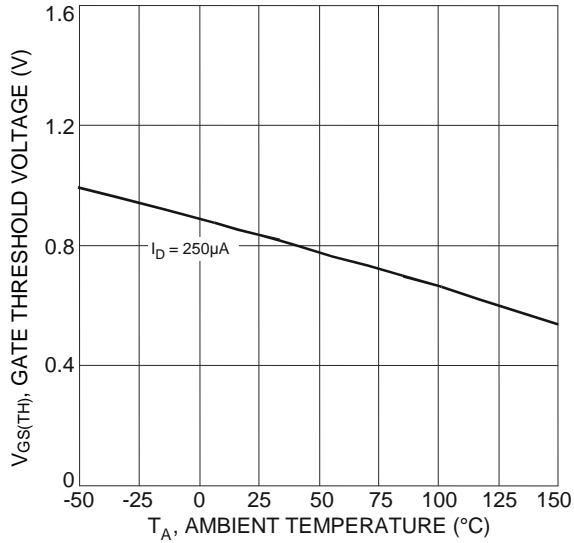


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

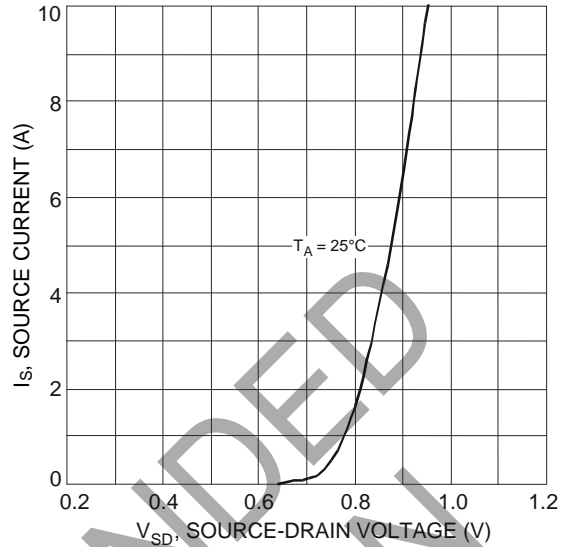


Fig. 8 Diode Forward Voltage vs. Current

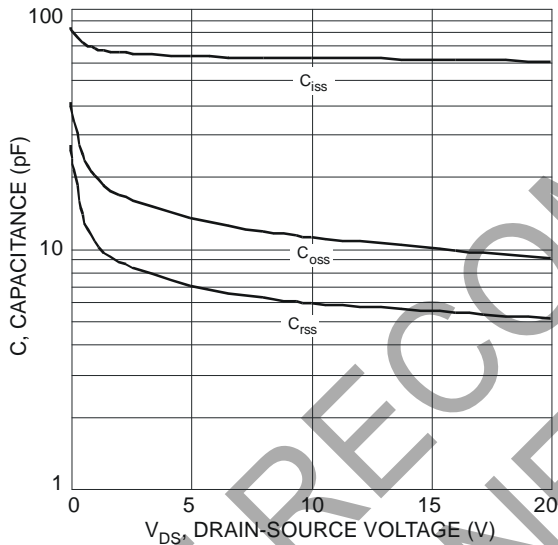


Fig. 9 Typical Capacitance

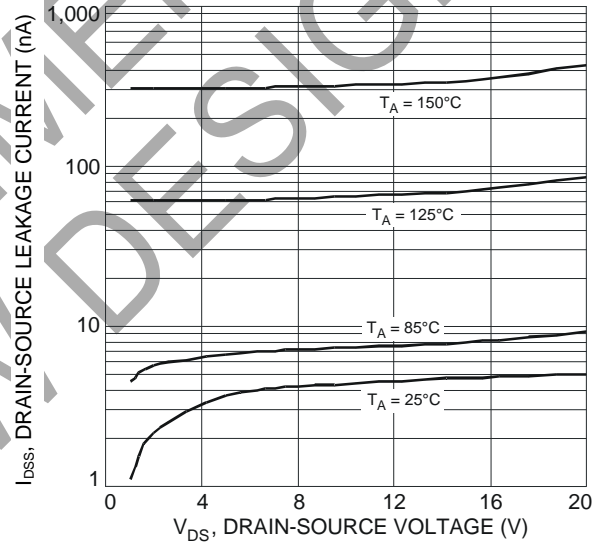
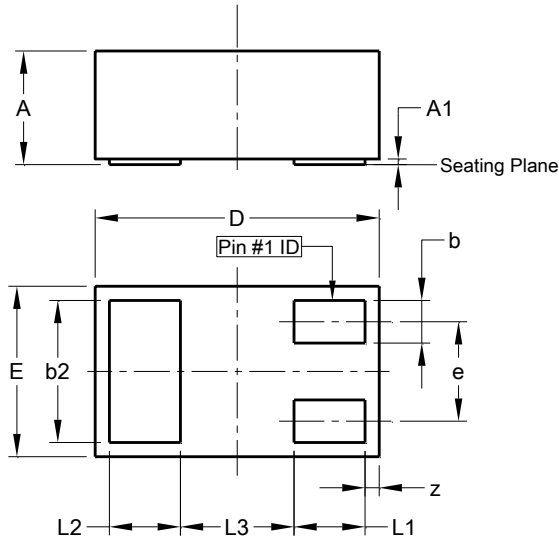


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X2-DFN1006-3

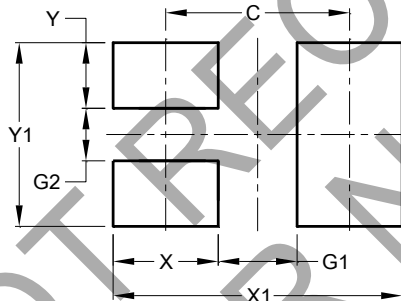


| X2-DFN1006-3 | | | |
|----------------------|------|------|------|
| Dim | Min | Max | Typ |
| A | — | 0.40 | — |
| A1 | 0.00 | 0.05 | 0.03 |
| b | 0.10 | 0.20 | 0.15 |
| b2 | 0.45 | 0.55 | 0.50 |
| D | 0.95 | 1.05 | 1.00 |
| E | 0.55 | 0.65 | 0.60 |
| e | - | - | 0.35 |
| L1 | 0.20 | 0.30 | 0.25 |
| L2 | 0.20 | 0.30 | 0.25 |
| L3 | - | - | 0.40 |
| z | 0.02 | 0.08 | 0.05 |
| All Dimensions in mm | | | |

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X2-DFN1006-3



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 0.70 |
| G1 | 0.30 |
| G2 | 0.20 |
| X | 0.40 |
| X1 | 1.10 |
| Y | 0.25 |
| Y1 | 0.70 |

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